

Silicon NPN Power Transistors

2SC3973B

DESCRIPTION

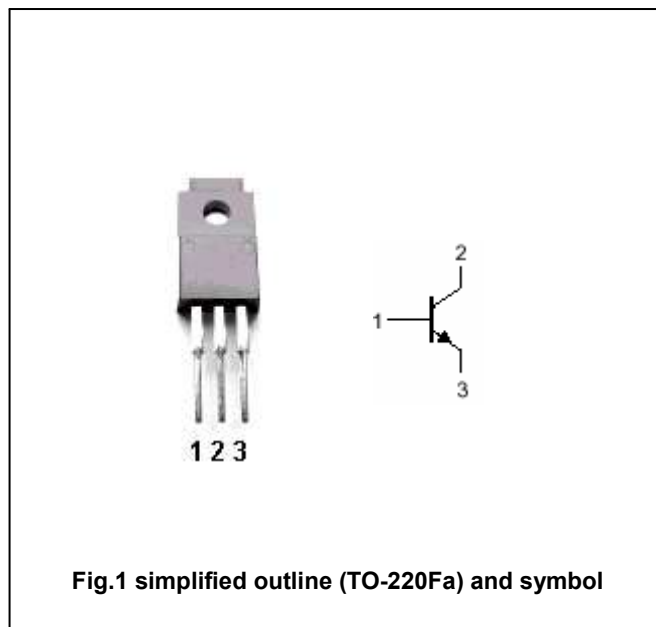
- With TO-220Fa package
- High voltage,high speed
- Wide area of safe operation

APPLICATIONS

- For high voltage,high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	8	V
I_C	Collector current (DC)		7	A
I_{CM}	Collector current-Peak		15	A
I_B	Base current (DC)		4	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	45	
T_j	Maximum operating junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	8			

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PACKAGE OUTLINE

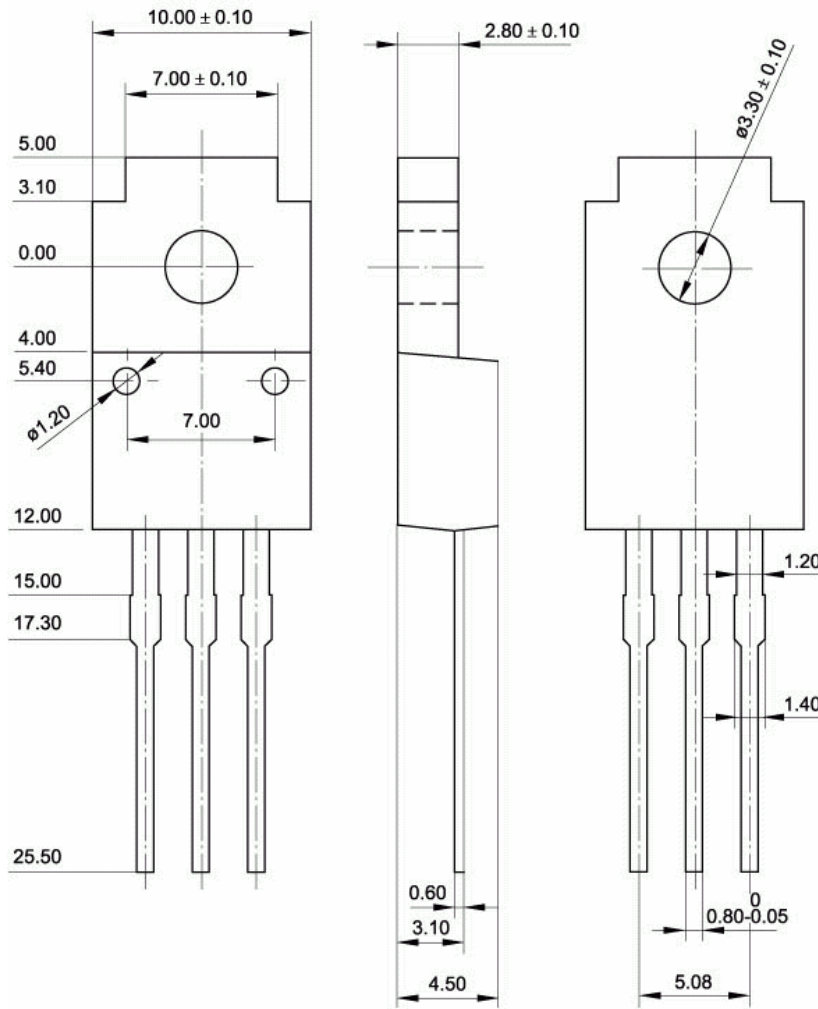


Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.